

## 6A, 1200V Hyperfast Dual Diode

The RHRP6120CC is a hyperfast dual diode with soft recovery characteristics ( $t_{RR} < 55\text{ns}$ ). It has half the recovery time of ultrafast diodes and is silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Formerly developmental type TA49058.

### PACKAGE AVAILABILITY

PART NUMBER	PACKAGE	BRAND
RHRP6120CC	TO-220AB	RHR6120C

NOTE: When ordering, use the entire part number.

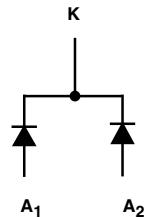
### Features

- Hyperfast with Soft Recovery ..... <55ns
- Operating Temperature ..... +175°C
- Reverse Voltage ..... 1200V
- Avalanche Energy Rated
- Planar Construction

### Applications

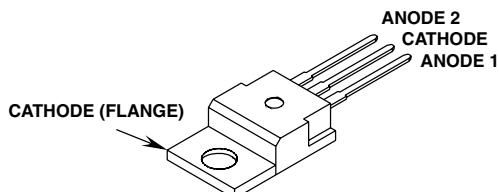
- Switching Power Supplies
- Power Switching Circuits
- General Purpose

### Symbol



### Packaging

JEDEC TO-220AB



## RHRP6120CC

### Absolute Maximum Ratings (Per Leg) $T_C = +25^\circ\text{C}$ , Unless Otherwise Specified

	RHRP6120CC	UNITS
Peak Repetitive Reverse Voltage.....	$V_{RRM}$	V
Working Peak Reverse Voltage.....	$V_{RWM}$	V
DC Blocking Voltage.....	$V_R$	V
Average Rectified Forward Current $T_C = 130^\circ\text{C}$	$I_{F(AV)}$	A
Repetitive Peak Surge Current..... Square Wave, 20kHz	$I_{FSM}$	A
Nonrepetitive Peak Surge Current..... Halfwave, 1 Phase, 60Hz	$I_{FSM}$	A
Maximum Power Dissipation.....	$P_D$	W
Avalanche Energy (See Figures 10 and 11).....	$E_{AVL}$	mJ
Operating and Storage Temperature.....	$T_{STG}, T_J$	${}^\circ\text{C}$
	-65 to +175	

*CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.*

### Electrical Specifications (Per Leg) $T_C = +25^\circ\text{C}$ , Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
$V_F$	$I_F = 6\text{A}, T_C = +25^\circ\text{C}$	-	-	3.2	V
	$I_F = 6\text{A}, T_C = +150^\circ\text{C}$	-	-	2.6	V
$I_R$	$V_R = 1200\text{V}, T_C = +25^\circ\text{C}$	-	-	100	$\mu\text{A}$
	$V_R = 1200\text{V}, T_C = +150^\circ\text{C}$	-	-	500	$\mu\text{A}$
$t_{RR}$	$I_F = 1\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	-	55	ns
	$I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	-	65	ns
$t_A$	$I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	33	-	ns
$t_B$	$I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	22	-	ns
$Q_{RR}$	$I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	210	-	nC
$C_J$	$V_R = 10\text{V}, I_F = 0\text{A}$	-	22	-	pF
$R_{\theta JC}$		-	-	3	${}^\circ\text{C}/\text{W}$

#### DEFINITIONS

$V_F$  = Instantaneous forward voltage ( $pw = 300\mu\text{s}$ ,  $D = 2\%$ ).

$I_R$  = Instantaneous reverse current.

$t_{RR}$  = Reverse recovery time (See Figure 9), summation of  $t_A + t_B$ .

$t_A$  = Time to reach peak reverse current (See Figure 9).

$t_B$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 9).

$Q_{RR}$  = Reverse recovery charge.

$C_J$  = Junction Capacitance.

$R_{\theta JC}$  = Thermal resistance junction to case.

$E_{AVL}$  = Controlled Avalanche Energy (See Figures 10 and 11).

$pw$  = pulse width.

$D$  = duty cycle.

### Typical Performance Curves

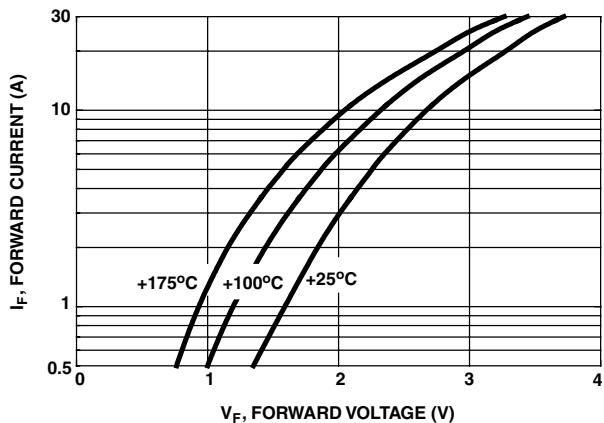


FIGURE 1. TYPICAL FORWARD CURRENT vs FORWARD VOLTAGE DROP

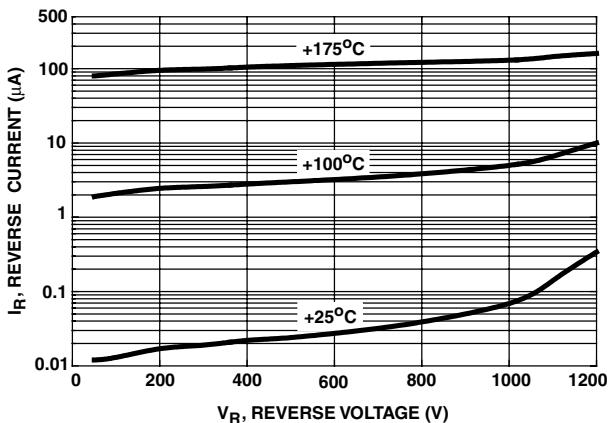


FIGURE 2. TYPICAL REVERSE CURRENT vs REVERSE VOLTAGE

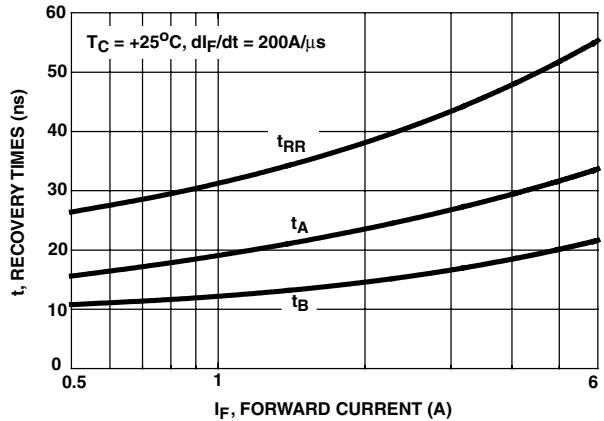


FIGURE 3. TYPICAL t<sub>RR</sub>, t<sub>A</sub> AND t<sub>B</sub> CURVES vs FORWARD CURRENT AT 25°C

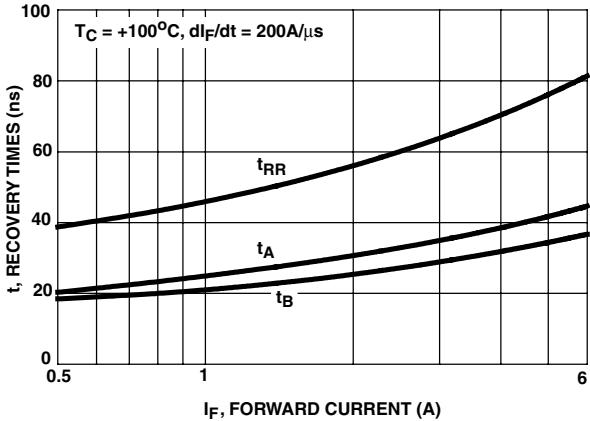


FIGURE 4. TYPICAL t<sub>RR</sub>, t<sub>A</sub> AND t<sub>B</sub> CURVES vs FORWARD CURRENT AT 100°C

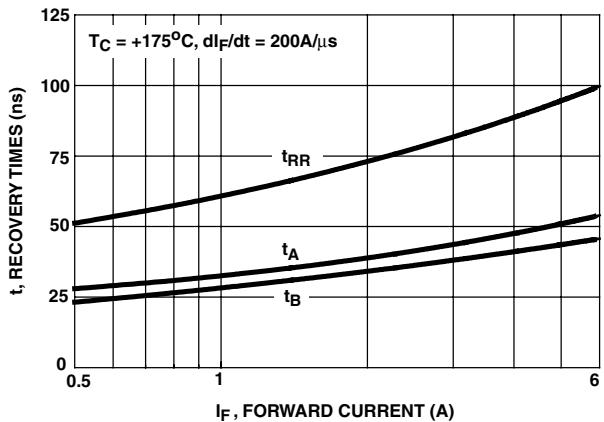


FIGURE 5. TYPICAL t<sub>RR</sub>, t<sub>A</sub> AND t<sub>B</sub> CURVES vs FORWARD CURRENT AT 175°C

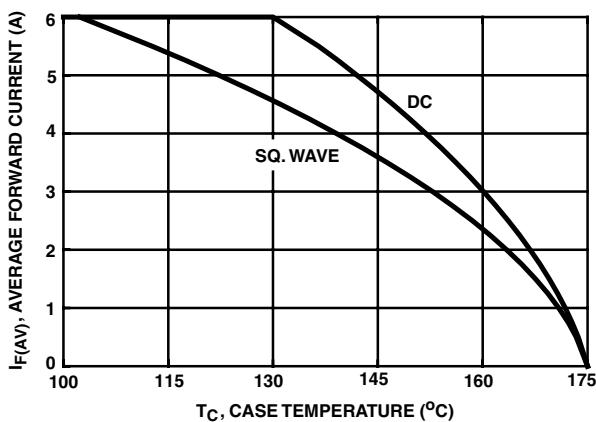


FIGURE 6. CURRENT DERATING CURVE

**Typical Performance Curves** (Continued)

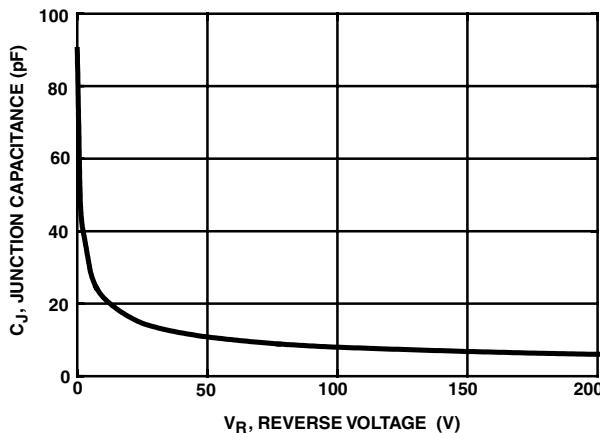


FIGURE 7. TYPICAL JUNCTION CAPACITANCE vs REVERSE VOLTAGE

**Test Circuits and Waveforms**

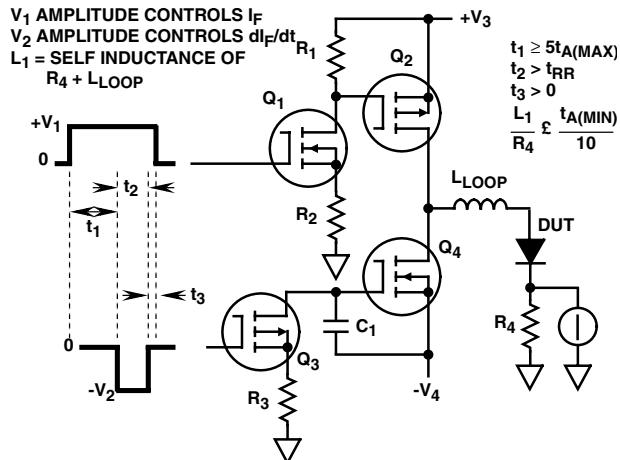


FIGURE 8.  $t_{RR}$  TEST CIRCUIT

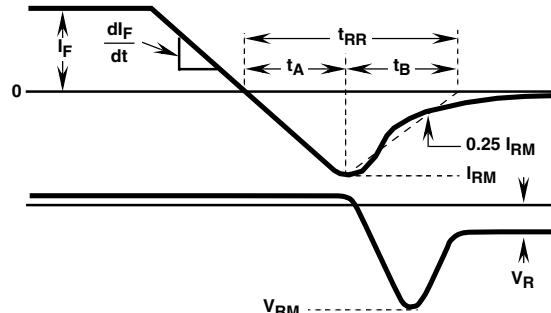


FIGURE 9.  $t_{RR}$  WAVEFORMS AND DEFINITIONS

$L = 40\text{mH}$   
 $R < 0.1\Omega$   
 $E_{AVL} = 1/2L^2 [V_{AVL}/(V_{AVL} - V_{DD})]$   
 Q<sub>1</sub> AND Q<sub>2</sub> ARE 1000V MOSFETs

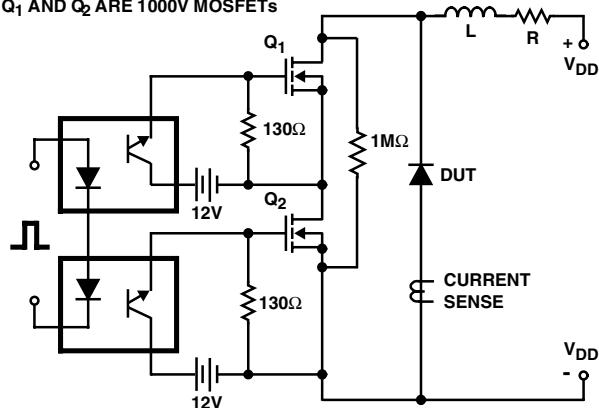


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

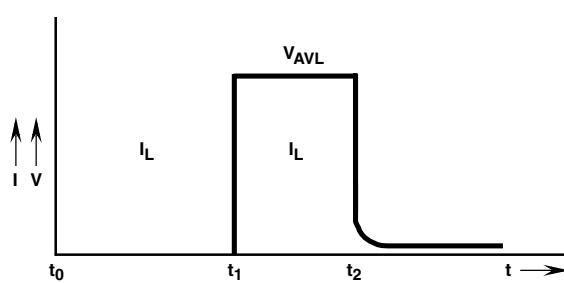
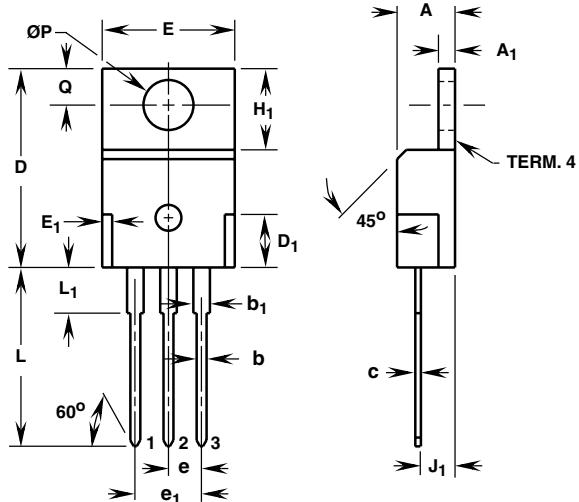


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

**TO-220AB**

3 LEAD JEDEC TO-220AB PLASTIC PACKAGE



LEAD 1. ANODE 1  
LEAD 2. CATHODE  
LEAD 3. ANODE 2  
TERM. 4. CATHODE

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.170	0.180	4.32	4.57	-
A <sub>1</sub>	0.048	0.052	1.22	1.32	-
b	0.030	0.034	0.77	0.86	3, 4
b <sub>1</sub>	0.045	0.055	1.15	1.39	2, 3
c	0.014	0.019	0.36	0.48	2, 3, 4
D	0.590	0.610	14.99	15.49	-
D <sub>1</sub>	-	0.160	-	4.06	-
E	0.395	0.410	10.04	10.41	-
E <sub>1</sub>	-	0.030	-	0.76	-
e	0.100 TYP		2.54 TYP		5
e <sub>1</sub>	0.200 BSC		5.08 BSC		5
H <sub>1</sub>	0.235	0.255	5.97	6.47	-
J <sub>1</sub>	0.100	0.110	2.54	2.79	6
L	0.530	0.550	13.47	13.97	-
L <sub>1</sub>	0.130	0.150	3.31	3.81	2
ØP	0.149	0.153	3.79	3.88	-
Q	0.102	0.112	2.60	2.84	-

NOTES:

1. These dimensions are within allowable dimensions of Rev. J of JEDEC TO-220AB outline dated 3-24-87.
2. Lead dimension and finish uncontrolled in L<sub>1</sub>.
3. Lead dimension (without solder).
4. Add typically 0.002 inches (0.05mm) for solder coating.
5. Position of lead to be measured 0.250 inches (6.35mm) from bottom of dimension D.
6. Position of lead to be measured 0.100 inches (2.54mm) from bottom of dimension D.
7. Controlling dimension: Inch.
8. Revision 1 dated 1-93.

## TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FAST®	PACMAN™	SuperSOT™-3
Bottomless™	FASTR™	POP™	SuperSOT™-6
CoolFET™	GlobalOptoisolator™	PowerTrench®	SuperSOT™-8
CROSSVOLT™	GTO™	QFET™	SyncFET™
DenseTrench™	HiSeC™	QS™	TinyLogic™
DOME™	ISOPLANAR™	QT Optoelectronics™	UHC™
EcoSPARK™	LittleFET™	Quiet Series™	UltraFET®
E <sup>2</sup> CMOS™	MicroFET™	SILENT SWITCHER®	VCX™
EnSigna™	MICROWIRE™	SMART START™	
FACT™	OPTOLOGIC™	Star* Power™	
FACT Quiet Series™	OPTOPLANAR™	Stealth™	

## DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

## LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.